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| Substitute for form 1449A/PTO | | | | <i>Complete if Known</i> | |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i> | | | | Application Number | 10/642,305 |
| | | | | Filing Date | August 18, 2003 |
| | | | | First Named Inventor | Hongyong ZHANG et al. |
| | | | | Art Unit | 2811 |
| | | | | Examiner Name | Douglas W. Owens |
| Sheet | 1 | of | 1 | Attorney Docket Number | 740756-2646 |
| OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS | | | | | |
| Examiner Initials ¹ | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | | | |
| /DWO/ | | LEE, M.K. et al. "Control of Silicon Dioxide Properties by RF Sputtering", <u>Journal of the Electrochemical Society</u> , Vol. 130, No. 3, (March 1983) pp. 658-659. | | | |
| /DWO/ | | Expert Report on the Invalidity of U.S. Patents 5,352,291, Zhang et al. No. 6,177,302B1, Yamazaki et al., and No. 6,566,175B2, Yamazaki et al., by S. Wagner, September 24, 2006 | | | |
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(List I)

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| /DWO/ | 1 | Toppoly's Opposition Claim Construction Brief, May 30, 2006 | | |
| /DWO/ | 2 | Declaration of Hector G. Gallegos in Support of Toppoly Optoelectronics Corp's. Opposition Claim Construction Brief, May 30, 2006 | | |
| /DWO/ | 3 | Plaintiff and Counterclaim Defendant Semiconductor Energy Laboratory Co., Ltd.'s Memorandum of Points and Authorities in Opposition to Defendants' and Counterclaim Plaintiffs' Claim Construction Brief (signed on 05/26/2006), May 30, 2006 | | |
| /DWO/ | 4 | Supplemental Declaration of Reginald J. Hill in Support of Semiconductor Energy Laboratory Co., Ltd.'s Claim Constructions (signed on 05/26/2006); May 30, 2006 | | |
| /DWO/ | 5 | Toppoly Optoelectronics Corp.'s Supplemental Response to Semiconductor Energy Laboratory Co., Ltd.'s Interrogatory No. 4, June 21, 2006 | | |
| /DWO/ | 6 | Order: Claim Construction Ruling, July 25, 2006 | | |
| /DWO/ | 7 | Invalidity Report of Professor Gottlieb S. Oehrlein, September 22, 2006 | | |
| /DWO/ | 8 | Expert on the Invalidity of U.S. Patents 5,352,291, Zhang et al. No. 6,177,302B1, Yamazaki et al., and No. 6,566,175B2, Yamazaki et al., by S. Wagner, September 24, 2006 | | |
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(List 2-3)

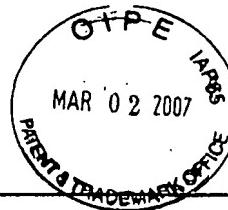
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| /DWO/ | | ROHATGI A., et al. "Chlorine Incorporation in HCl Oxides", <u>Journal of The Electrochemical Society</u> , Vol. 126, No. 1, (January 1979), pp. 143-148. | | |
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| /DWO/ | | Exhibit 7, Asserted Claim Chart – Sano Reference, JP 64-35959 | |
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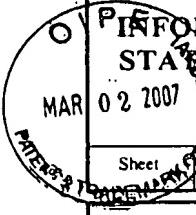
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| /DWO/ | | US-4,007,294 | | 02/08/1977 | Woods et al. |
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